

# **DISTINCTIVE CHARACTERISTICS**

- Logic voltage levels compatible with TTL
- Three-state output buffers and common I/O
- I<sub>CC</sub> Max., as low as 100 mA

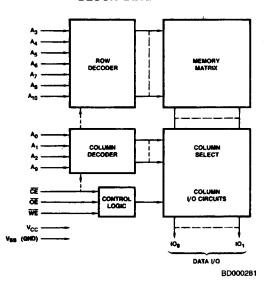
- tAA/tACS as low as 70 ns
- Power-Down mode (ISB as low as 15 mA)

#### GENERAL DESCRIPTION

The Am9128 is a 16,384-bit Static Random = Access Read-write Memory organized as 2048 words of 8 bits. It uses fully static circuitry, requiring no clocks or refresh to operate. Directly TTL-compatible inputs and outputs and operation from a single +5 V supply simplify system

designs. Common data I/O pins using three-state outputs are provided. The Am9128 is available in an industry-standard 24-pin DIP package with 0.6-inch pin row spacing. The Am9128 uses the JEDEC standard pinout for byte-wide memories (compatible to 16K EPROMs).

# **BLOCK DIAGRAM**



#### PRODUCT SELECTOR GUIDE

Part Nu	mber	Am9128-70	Am9128-90	Am9128-10	Am9128-12	Am9128-15	Am9128-20		
Maximum Access Time (ns)		70	90	100	120	150	200		
Maximum Operat-	0 to 70°C	140	N/A	120	N/A	100	140		
ing Current (mA)	-55° to 125°C	N/A	180	N/A	150	150	150		
Maximum Standby	0° to 70°C	0° to 70°C	0° to 70°C	30	N/A	15	N/A	15	30
Current (mA)	-55° to 125°C	N/A	30	N/A	30	30	30		

# CONNECTION DIAGRAMS Top View

DIPs V<sub>CC</sub>(+5 V) 24 23 A<sub>8</sub> 22 WE A4 [ 21 ₽ A<sub>3</sub> [ 20 ] A<sub>10</sub> A<sub>2</sub> [ 19 CE A<sub>1</sub> 18 108 **₩** [ 17 ] IO<sub>7</sub> Ю1 [ 16 106 Ю2 [ 10 15 Ю5 V<sub>88</sub> (GND) 104 13

CD000121

Note: Pin 1 is marked for orientation.

# METALLIZATION AND PAD LAYOUT

Address Designators						
External	Internal					
A <sub>3</sub>	AX <sub>0</sub>					
A4	AX <sub>1</sub>					
A <sub>5</sub>	AX <sub>2</sub>					
A <sub>6</sub>	АХз					
A <sub>7</sub>	AX4					
A <sub>8</sub>	AX5					
A <sub>10</sub>	AX <sub>6</sub>					
A <sub>0</sub>	AY <sub>0</sub>					
A <sub>1</sub>	AY <sub>1</sub>					
A <sub>2</sub>	AY2					
Ag	AY3					



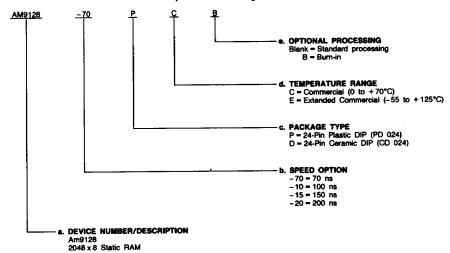
DIE SIZE: 0.162" x 0.240"

# ORDERING INFORMATION

#### Standard Products

AMD standard products are available in several packages and operating ranges. The order number (Valid Combination) is formed by a combination of: a. Device Number

- b. Speed Option (if applicable)
- c. Package Type
- d. Temperature Range
- e. Optional Processing



Valid C	Valid Combinations							
AM9128-70								
AM9128-10	PC, DC, DCB, DE,							
AM9128-15	DEB							
AM9128-20	1							

#### Valid Combinations

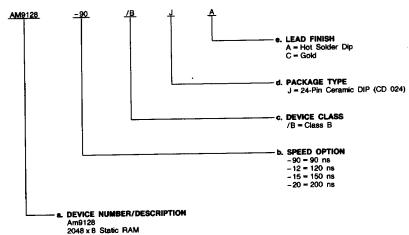
Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMD sales office to confirm availability of specific valid combinations, to check on newly released combinations, and to obtain additional data on AMD's standard military grade products.

# ORDERING INFORMATION

#### **APL Products**

AMD products for Aerospace and Defense applications are available in several packages and operating ranges. APL (Approved Products List) products are fully compliant with MIL-STD-883C requirements. The order number (Valid Combination) for APL products is formed by a combination of: a. Device Number

- b. Speed Option (if applicable)
- c. Device Class
- d. Package Type
- e. Lead Finish



Valid Combinations							
AM9128-90							
AM9128-12	/BJA, /BJC						
AM9128-15	7534, 7530						
AM9128-20	]						

#### Valid Combinations

Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMD sales office to confirm availability of specific valid combinations or to check for newly released valid combinations.

# Group A Tests

Group A tests consist of Subgroups 1, 2, 3, 7, 8, 9, 10, 11

# PIN DESCRIPTION

# A<sub>0</sub> - A<sub>10</sub> Addresses (Input)

The 10-bit field presented at the address inputs selects one of the 2048 memory locations to be read from — or written into — via the data lines.

# I/O1-I/O8 Data In/Out Port (Input/Output)

If  $\overline{WE}$  is LOW, the data represented on the I/O lines can be written into the selected memory location. If  $\overline{WE}$  is HIGH, the I/O lines represent the data read from the selected memory location.

#### CE Chip Enable (Input, Active LOW)

Read and Write cycles can be executed only when CE is LOW.

#### WE Write Enable (Input, Active LOW)

Data is written into the memory if WE is LOW and read from the memory if WE is HIGH.

#### OE Output Enable (Input, Active LOW)

Read cycles can be executed only when OE is LOW.

# ABSOLUTE MAXIMUM RATINGS (Note 11)

Storage Temperature	65 to +150°C
Ambient Temperature with	
Power Applied	55 to +125°C
Supply Voltage	
Signal Voltage with	
Respect to Ground	3.0 V to +7.0 V
Power Dissipation	1.0 W
DC Output Current	

<sup>\*</sup>Maximum ratings are to be for system design reference, parameters given may not be 100% tested by AMD.

Stresses above those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent device failure. Functionality at or above these limits is not implied. Exposure to absolute maximum ratings for extended periods may affect device reliability.

# **OPERATING RANGES** (Note 3)

Commercial (C) Devices	0 to ±70°C
Ambient Temperature (T <sub>A</sub> ) Supply Voltage (V <sub>CC</sub> )	. +4.5 V to +5.5 V
Military* (M) and Extended Commercia	I (E) Devices
Case Temperature (TA)	55 to +125°C
Supply Voltage (VCC)	. +4.5 V to +5.5 V

Operating ranges define those limits between which the functionality of the device is guaranteed.

DC CHARACTERISTICS over operating ranges unless otherwise specified (for APL Products, Group A, Subgroups 1, 2, 3 are tested unless otherwise noted) (Note 3)

	_		Am9128-90 Am9128-10		Am9128-15		Am9128-70 Am9128-12 Am9128-20			
Parameter Symbol	Parameter Description	Test Conditions		Min.	Max.	Min.	Max.	Min.	Max.	Unit
ЮН	Output HIGH Current	V <sub>OH</sub> = 2.4 V	V <sub>CC</sub> = 4.5 V	-2		-2		-2		mΑ
lOL	Output LOW Current	V <sub>OL</sub> = 0.4 V	VCC - 4.5 V	4		4		4		mA
VIH	Input HIGH Voltage			2.0	V <sub>0</sub> C +1.0	2.0	VCC + 1.0	2.0	V <sub>CC</sub> + 1.0	v
VIL	Input LOW Voltage			-0.5	0.8	-0.5	0.8	-0.5	0.8	٧
lix	Input Load Current	V <sub>SS</sub> < V <sub>I</sub> < V <sub>CC</sub>			10		10		10	μА
loz	Output Leakage Current	V <sub>SS</sub> ≤ V <sub>O</sub> ≤ V <sub>CC</sub> Output Disabled			10		10		10	μА
C <sub>IN</sub>	Input Capacitance (Note 12)	Test Frequency = 1.0 MHz,			6		6		6	_
C <sub>I/O</sub>	Input/Output Capacitance (Note 12)	TA = 25°C, All pins at 0	V <sub>CC</sub> = 5.0 V		7		7		7	pF
		11. U OF 24	COM'L		120		100	140		
loc	V <sub>CC</sub> Operating Supply Current	Max. V <sub>CC</sub> , CE ≤ V <sub>IL</sub> Outputs Open	MIL/E- COM'L		180		150	150		mA
			COM'L		15		15	30		
ISB	Automatic CE Power Down Current	Max. V <sub>CC</sub> , CE ≥ V <sub>IH</sub>	MIL/E- COM'L		30		30	30		mA
		V 000 4- V- 11-	COM'L		15		15	30		
lPO	Peak Power On Current (Note 12)	V <sub>CC</sub> = GND to V <sub>CC</sub> Max. CE ≥ V <sub>IH</sub> (Note 2)	MIL/E- COM'L		30		30	30		mA

- Notes: 1. The internal write time of the memory is defined by the overlap of CE LOW and WE LOW. Both signals must be LOW to initiate a write and either signal can terminate a write by going HIGH. The data input setup and hold timing should be referenced to the rising edge of the signal that terminates the write.

  2. A pull up resistor to V<sub>CC</sub> on the CE input is required during power up to keep the device deselected, otherwise I<sub>PO</sub> will exceed values given.

  3. For test and correlation purposes, ambient temperature is defined as the "Instant-on" case temperature.

  4. At any given temperature and voltage condition, t<sub>HZ</sub> is less than t<sub>LZ</sub>.

  5. WE is HIGH for read cycle.

  6. Device is continuously selected, CE = V<sub>IL</sub>.

  7. Address valid prior to or coincident with CE transition LOW.

  8. OE = V<sub>IL</sub>.

  9. C. = 3.0 c.

  - 9. CL = 30 pF.
  - 10. Transition is measured from 1.5 V on the input to VOH 500 mV and VOL+ 500 mV on the outputs using the load shown in Switching Test Circuits. C<sub>L</sub> = 5 pF.
  - 11. The products described by this specification include internal circuitry designed to protect input devices from damaging accumulations of static charge. It is suggested, nevertheless, that conventional precautions be observed during storage, handling, and use to avoid exposure to excessive voltages.
  - 12. The parameter is guaranteed by characterization, but is not tested.

**SWITCHING CHARACTERISTICS** over operating ranges unless otherwise specified (for APL Products, Group A, Subgroups 9, 10, 11 are tested unless otherwise noted.)

Am9128-70, -90, -10

MDOI YCLE TRC	Parameter Description  Read Cycle Time Address Access Time (Note Chip Select Access Time (I Output Enable Time (Note 9)		<b>Min.</b>	70 70	<b>Min.</b> 90	Max.	Min.	Max	Unit ns
ACC ACS IOE	Address Access Time (Note Chip Select Access Time (I Output Enable Time (Note 9)	Note 9) COM*L	70		90	90	100	100	
ACC ACS TOE	Address Access Time (Note Chip Select Access Time (I Output Enable Time (Note 9)	Note 9) COM*L	70		90	90	100	100	
ACS TOE	Chip Select Access Time (I Output Enable Time (Note 9)	Note 9) COM*L				90		1 100 1	ne.
toe toн	Output Enable Time (Note 9)	COM'L		70					
тон	(Note 9)					90		100	ns
тон	(Note 9)	Adl		40		N/A	ļ	50	ns
	Output Hold Time from Adv	MIL		N/A		50		N/A	<b>└</b>
CLZ	Output Hold Time from Address Change		5		5		5	ļ	ns
	Output in Low-Z from CE (Notes 4, 10, 12)		5		5		5		ns
CHZ	Output in Hi-Z from CE (Notes 4, 10, 12)			35		40		40	ns
OLZ	Output in Low-Z from OE (Notes 4, 10, 12)		5	l	5		5		ns
OHZ	Output in Hi-Z from OE (Notes 4, 10, 12)			30		35		35	ns
teu	Chip Selection to Power-Up Time (Note 12)		0		0		0		ns
tPO	Chip Deselection to Power-Down Time (Note 12)			40		45		50	ns
CYCLE									
twc	Write Cycle Time		70		90		100		ns
<del>"""</del>	Chip Selection to	0 to +70°C	60		N/A	1	90	İ	l ns
tcw	End of Write (Note 1)	-55 to -125°C	N/A		80		N/A		] "
100			5		10		10		ns
		1	40		55		60		ns
	******	<u></u>	5		5		5		ns
			30		35		40		ns
			5	1	5	T	5		ns
		(Notes 4, 10, 12)	5	1	5		5		ns
				30	1	35		35	ns
		10100 17 177 127	65	1	80		60	1	ns
Child Child The transfer to th	PU PO YCLE	Output in Hi-Z from OE (Note) Chip Selection to Power-Up Chip Deselection to Power VCLE Word Write Cycle Time Chip Selection to End of Write (Note 1)  AS Address Setup Time Why Write Pulse Width (Note 1) Why Write Recovery Time DB Data Setup Time DB Data Setup Time DB Data Hold Time Output in Low-Z from WE WHZ Output in Hi-Z from WE (Note)	Output in Hi-Z from OE (Notes 4, 10, 12)  PU Chip Selection to Power-Up Time (Note 12)  PO Chip Deselection to Power-Down Time (Note 12)  YCLE  Write Cycle Time  CW Chip Selection to End of Write (Note 1)  AS Address Setup Time  Write Pulse Width (Note 1)  Write Recovery Time  DB Data Setup Time  DB Data Setup Time  DH Data Hold Time  Output in Low-Z from WE (Notes 4, 10, 12)  WHZ Output in Hi-Z from WE (Notes 4, 10, 12)	Couput in Hi-Z from OE (Notes 4, 10, 12)		Digital College	Disput in Low-2 from OE (Notes 4, 10, 12)	Dutput in Low-Z from DE (Notes 4, 10, 12)   30   35	Ditz         Output in Low-Z from OE (Notes 4, 10, 12)         30         35         35           HZ         Output in Hi-Z from OE (Notes 4, 10, 12)         0         0         0         0           PU         Chip Selection to Power-Up Time (Note 12)         0         0         0         0           PO         Chip Deselection to Power-Down Time (Note 12)         40         45         50           YCLE         NC         Write Cycle Time         70         90         100           NC         Chip Selection to End of Write (Note 1)         0 to +70°C         60         N/A         90           CW         End of Write (Note 1)         -55 to -125°C         N/A         80         N/A           AA         Address Setup Time         5         10         10           WWP         Write Pulse Width (Note 1)         40         55         60           WR         Write Recovery Time         5         5         5           DS         Data Setup Time         30         35         40           DH         Data Hold Time         5         5         5           WHZ         Output in Low-Z from WE (Notes 4, 10, 12)         5         5         5           WHZ

Notes: See notes following DC Characteristics table.

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# SWITCHING CHARACTERISTICS (Cont'd.)

Am9128-12, -15, -20

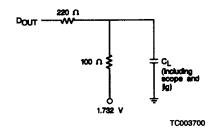
				Am91	28-12	Am91	26-15	Am9128-20		
No.	Parameter Symbol		meter ription	Min.	Max.	Min.	Max.	Min.	Max.	Unit
RE	AD CYCLE									
1	tRC	Read Cycle Time		120		150		200		ns
2	tACC	Address Access Time (Not	e 9)		120		150		200	ns
3	tacs	Chip Select Access Time (Note 9)			120		150		200	ns
		Output Enable Time	COMIL	· I	N/A		60		70	ns
4	tOE	(Note 9)	MIL		70		70		80	80
5	ф	Output Hold Time from Address Change		5		5	L	5	L	ns
6	tCLZ	Output in Low-Z from CE (Notes 4, 10, 12)		5		5		5	L	ns
7	tcHZ	Output in Hi-Z from CE (Notes 4, 10, 12)			50	<u> </u>	55		55	กร
8	toLZ	Output in Low-Z from OE (Notes 4, 10, 12)		5	]	5		5	<u> </u>	ns
9	tonz tonz	Output in Hi-Z from OE (Notes 4, 10, 12)			45	I	50		50	ns
10	teu	Chip Selection to Power-Up Time (Note 12)		0		0		0	ļ	ns
11	t <sub>PD</sub>	Chip Deselection to Power-Down Time (Note 12)			55		60		60	ns
WI	RITE CYCLE									
12	twc	Write Cycle Time		120		150		200	<u> </u>	ns
		Chip Selection to	COMIL	N/A		120	Ī	150	L	ns
13	tcw	End of Write (Note 1)	MIL	105		130		160		
14	tas	Address Setup Time		10		20	Ι	20		ns
15	twp	Write Pulse Width (Note 1	)	70		85		100		ns
16	twn	Write Recovery Time		5	1	5		5		ns.
17	tos	Data Setup Time		45		50		60		ns
18	t <sub>DH</sub>	Data Hold Time		5		5		5		ns
19	twiz	Output in Low-Z from WE	(Notes 4, 10, 12)	5		5		5	L	ns
20	twnz	Output in Hi-Z from WE (f	Notes 4, 10, 12)		50		50		50	ne
21	taw	Address to End of Write		105		120		120		ns

Notes: See notes following DC Characteristics table.

# SWITCHING TEST CONDITIONS

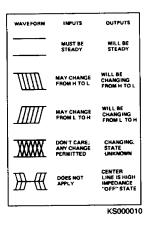
Input Pulse Levels	.4 to 2.4 V
Input Rise and Fall Times	10 ns
Input Timing Reference Levels	1.4 V
Output Timing Reference Levels	1.4 V

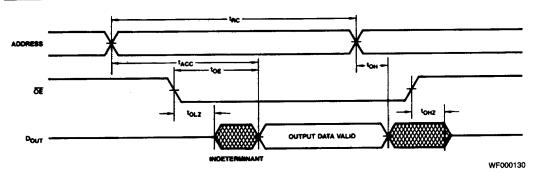
# SWITCHING TEST CIRCUIT



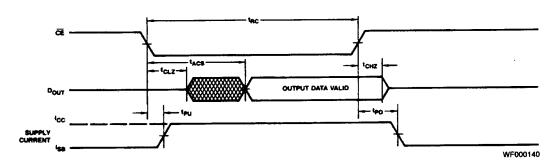
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# SWITCHING WAVEFORMS KEY TO SWITCHING WAVEFORMS





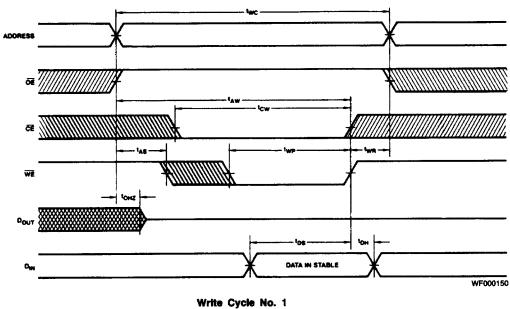
Read Cycle No. 1 (Notes 5, 6)

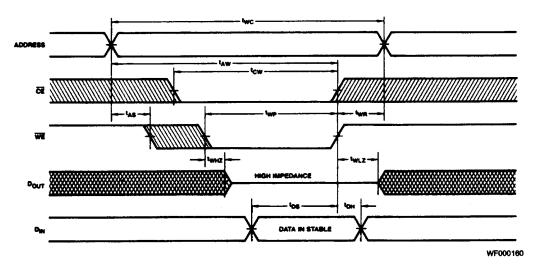


Read Cycle No. 2 (Notes 5, 7, 8)

Notes: See notes following DC Characteristics table.

# SWITCHING WAVEFORMS (Cont'd.)





Write Cycle No. 2 (Notes 7, 8)

Notes: See notes following DC Characteristics table.

# TYPICAL PERFORMANCE CURVES

